

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	8900	GaN	USPAT
2	BRS	L2	575	1 and roughness	USPAT
3	BRS	L3	51	2 and (contact adj resistance)	USPAT
4	BRS	L4	744	roughness with (source or drain)	USPAT
5	BRS	L5	22	1 and 4	USPAT
6	BRS	L6	66	2 and schottky	USPAT
7	BRS	L7	235	2 and transistor	USPAT

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	27117	GaN	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	794	1 and roughness	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	75	2 and (contact adj resistance)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	0	("2004/0201038").URPN.	USPAT
5	BRS	L5	1077	roughness with (source or drain)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	17	1 and 5	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L8	276	2 and transistor	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L7	76	2 and schottky	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	276	2 and transistor	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB